

FORM PTO-1449 (REV.7-80)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 500462.04	APPLICATION NO. Not Yet Assigned
		APPLICANT(S) Wendell P. Noble	
		FILING DATE Concurrently herewith	GROUP ART UNIT Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT
(Use several sheets if necessary)
U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
EM	AA	4,810,667	03/07/89	Zorinsky et al.	437	62	
	AB	4,881,105	11/14/89	Davari et al.	357	23.4	
	AC	5,194,396	03/16/93	Kim et al.	437	31	
	AD	5,574,299	11/12/96	Kim	257	296	
	AE	5,592,005	01/07/97	Floyd et al.	257	331	
	AF	5,594,683	01/14/97	Chen et al.	365	177	
	AG	6,075,272	06/13/00	Forbes et al.	257	378	
	AH	6,229,161 B1	05/08/01	Nemati et al.	257	133	
EQ	AI	6,489,192 B2	12/03/02	Noble	438	202	

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
EQ	AJ	JP359232437A	12/27/84	Japan			X	
EQ	AK	10135235	05/22/98	Japan			X	

OTHER PRIOR ART *(Including Author, Title, Date, Pertinent Pages, Etc.)*

EQ	AL	S.D. Malaviya, "Single Device DC Stable Memory Cell", IBM Technical Disclosure Bulletin, Vol. 20, No. 9, February 1978, IBM Corp. 1978, 3492-3494.
	AM	Jack Y.C. Sun, "CMOS Technology for 1.8V and Beyond", Semiconductor Research and Development Center, IBM Corporation, pp. 293-297.
	AN	Sakui, Koji et al., "A New Static Memory Cell Based on Reverse Base Current (RBC) Effect of Bipolar Transistor", ULSI Research Center, Toshiba Corporation, Japan, 44-IEDM 88 (4 pages).
	AO	Van der Wagt, J.P., et al., "RTD/HFET Low Standby Power SRAM Gain Cell", IEEE Electron Device Letters, Vol. 19, No. 1, January 1998, pp. 6-9.
EQ	AP	Verdonckt-Vandebroek, Sophie et al., "Hight-Gain Lateral Bipolar Action in a MOSFET Structure", IEEE Transactions on Electron Devices, Vol. 38, No. 11, November 1991, pp. 2487-2496.

EXAMINER

EQ

DATE CONSIDERED

1125-04

* EXAMINER: Initial if reference considered, whether or not criteria is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).